

TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

MT4S07U

VHF~UHF Band Low Noise Amplifier Applications

- Low Noise Figure: $NF = 1.5\text{dB}$
($V_{CE} = 3\text{ V}$, $I_C = 5\text{ mA}$, $f = 2\text{ GHz}$)
- High Gain: $|S_{21e}|^2 = 10.5\text{dB}$
($V_{CE} = 3\text{ V}$, $I_C = 15\text{ mA}$, $f = 2\text{ GHz}$)

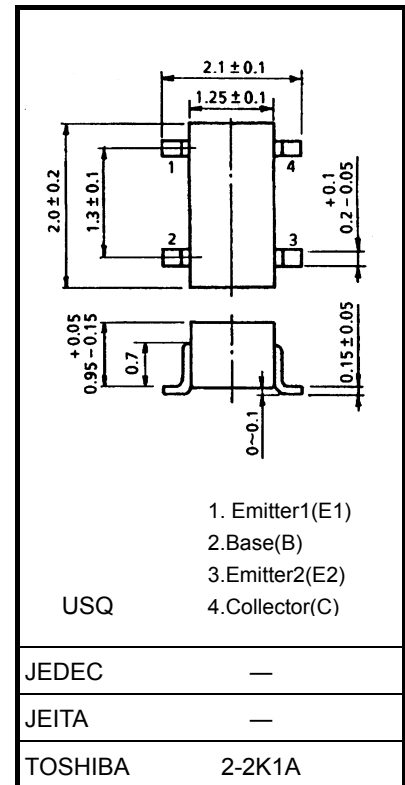
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	10	V
Collector-emitter voltage	V_{CEO}	5	V
Emitter-base voltage	V_{EBO}	1.5	V
Collector current	I_C	25	mA
Base current	I_B	10	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55~125	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

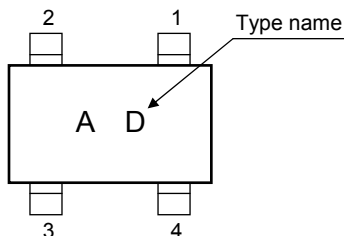
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Unit: mm



Weight: 0.006 g (typ.)

Marking



Microwave Characteristics (Ta = 25°C)

Characteristic	Symbol	Condition	Min	Typ.	Max	Unit
Transition frequency	f_T	$V_{CE} = 3 \text{ V}, I_C = 10 \text{ mA}$	10	12	—	GHz
Insertion gain	$ S_{21e} ^2(1)$	$V_{CE} = 1 \text{ V}, I_C = 5 \text{ mA}, f = 2 \text{ GHz}$	—	8	—	dB
	$ S_{21e} ^2(2)$	$V_{CE} = 3 \text{ V}, I_C = 15 \text{ mA}, f = 2 \text{ GHz}$	7.5	10.5	—	
Noise figure	NF(1)	$V_{CE} = 1 \text{ V}, I_C = 5 \text{ mA}, f = 2 \text{ GHz}$	—	1.6	3	dB
	NF(2)	$V_{CE} = 3 \text{ V}, I_C = 5 \text{ mA}, f = 2 \text{ GHz}$	—	1.5	3	

Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 5 \text{ V}, I_E = 0$	—	—	0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 1 \text{ V}, I_C = 0$	—	—	1	μA
DC current gain	h_{FE}	$V_{CE} = 1 \text{ V}, I_C = 5 \text{ mA}$	70	—	140	—
Reverse transfer capacitance	C_{re}	$V_{CB} = 1 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ (Note)	—	0.4	0.85	pF

Note: C_{re} is measured with a three-terminal method using a capacitance bridge.

Caution

This device is sensitive to electrostatic discharge. Ensure that tools and equipment are sufficiently grounded before handling. When handling individual devices (which are not yet mounted on a circuit board), ensure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.

RESTRICTIONS ON PRODUCT USE

20070701-EN GENERAL

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